arXiv:cond-mat/0501622v2 [cond-mat.mes-hall] 22 May 2005

Conductance Fluctuations and Partially Broken Spin Symmetries in Quantum Dots

D. M. Zumbuhl, J. B. Miller, and C. M. Marcus
Department of Physics, Harvard University, Cambridge, Massachusetts 02138

D. Goldhaber-Gordon
Department of Physics, Stanford University, Stanford, California 94305

J. S. Harris, Jr.
Departement of Electrical Engineering, Stanford University, Stanford, California 94305

K. Campman and A. C. Gossard
Materials Department, University of California, Santa Barbara, California 93106

Conductance uctuations in GaAs quantum dots with spin-orbit and Zeeman coupling are investigated experimentally and compared to a random matrix theory formulation that de nes a number of regimes of spin symmetry depending on experimental parameters. Accounting for orbital coupling of the in-plane magnetic eld, which can break time-reversal symmetry, yields excellent overall agreement between experiment and theory.

PACS numbers: 73.23.Hk, 73.20.Fz, 73.50.Gr, 73.23.-b

The combination of con nement, spin-orbit (SO) coupling, and Zeeman splitting in semiconductor quantum dots gives rise to rich physics, including experimental access to interesting partially-broken spin symmetries [1] and a suppression of SO e ects due to con nement [1, 2, 3, 4, 5] that provides long spin lifetimes in small quantum dots [5, 6]. Further consequences of these combined e ects are that the con nement-induced suppression of SO e ects is lifted by adding a Zeeman eld [1, 2, 3] or by allowing spatial dependence of the SO coupling [7]. Because of the nite thickness of a two-dimensional electron gas, an in-plane magnetic eld B_k will have an orbital coupling that a ects the electron dispersion and can break time-reversal symmetry (TRS) [4, 8, 9, 10, 11, 12], adding additional complexity to this system.

This Letter presents an experimental study of mesoscopic conductance uctuations in quantum dots that possess both signi cant SO and Zeeman coupling. We nd that the B_k dependence of the variance of conductance uctuations, var$g$, with TRS explicitly broken by a perpendicular eld ($B_? \neq 0$, i.e., $B_? \quad (h=e)=A$, where A is the dot area) depends critically on the strength of SO coupling and dot size. This dependence can be understood in terms of spin symmetries partially broken by B_k and is in quantitative agreement with an appropriate random matrix theory (RMT) formulation [1]. We also nd that var$g(B_?;B_k)$ becomes independent of $B_?$ at large B_k due to B_k breaking TRS, consistent with previous results [4, 10]. Taking into account orbital coupling [8, 9], agreement between theory and experiment is excellent for both broken and unbroken TRS and various regimes of spin symmetry.

In quantum dots, e ects of Rashba and linear Dresselhaus SO coupling are suppressed due to con nement in the absence of Zeeman coupling [1, 2, 5]. For large Zeeman splitting or weak con nement, this suppression is lifted and new symmetry classes with partially broken spin symmetry appear. A random matrix theory (RMT) analysis of this system was developed by Aleiner et al. [1] and extended to include inhomogeneous SO coupling and interpolation between ensembles [1]. The RMT formulation identi es three symmetry parameters that govern the amplitude (variance) of conductance uctuations, var$g$ / $s=(\ )$. Here, $= \{1;2;4\}$ is the usual Dyson parameter re ecting TRS, $s = \{1;2\}$ accounts for Kramers degeneracy, and $= \{1;2\}$ characterizes mixing between Kramers pairs. With these parameters, spin symmetry may be either unbroken ($s = 2;\ = 1$), partially broken ($s = 1;\ = 1$) or fully broken ($s = 1;\ = 2$), causing a reduction of the variance by a factor of two each time spin symmetry is incrementally broken. Temperature and decoherence also reduce var(g), but ratios such as var$g(B_k)$/var$g(B_k = 0)$ are a ected only weakly.

Conductance uctuations are known to be reduced by SO and Zeeman coupling in bulk (disordered) mesoscopic samples, and theories [13, 14, 15] are in good agreement with experiments [16]. Recently, the combined e ects of SO and Zeeman coupling on magnetoresistance in bulk samples were investigated [11], reporting spin-induced breaking of TRS [12]. Experimental observation of partially broken spin symmetry, which has been theoretically predicted [1, 14], has to our knowledge not been previously reported. Results of Ref. [1] were used to explain existing data on var$g(B_? \neq 0;B_k)$ [3] as well as subsequent experiments on average conductance (weak localization and antilocalization) in quantum dots [4, 17]. There have been no comparable studies of conductance uctuations to investigate the various symmetry classes to our knowledge.

Four gate-de ned quantum dots of various sizes on two heterostructure wafers were measured (see Table 1 and

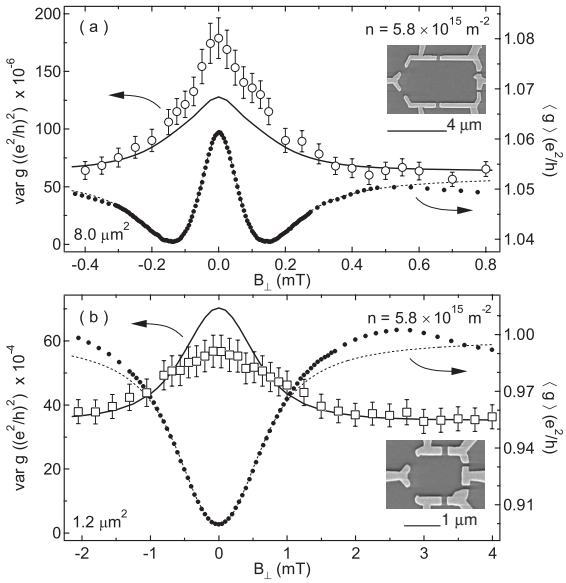

FIG. 1: Conductance average $\langle g(B_\perp)\rangle$ (solid dots) and variance $\mathrm{var}\, g(B_\perp)$ (open circles and squares) as a function of perpendicular magnetic field $B_\perp$ with $B_k = 0$, for large and small dots on the high density material, at $T = 300$ mK. (a) Antilocalization in $\langle g(B_\perp)\rangle$ for the 8 μm^2 dot. (b) Weak localization in $\langle g(B_\perp)\rangle$ for the 1.2 μm^2 dot, demonstrating confinement suppression of SO effects. Both dots show an enhancement of $\mathrm{var}\, g$ at $B_\perp = 0$. Fits of RMT [1] to $\langle g(B_\perp)\rangle$ (dashed curves) and $\mathrm{var}\, g(B_\perp)$ (solid curves) using fit parameters determined from fits to $\langle g\rangle$ plus an overall scale factor for $\mathrm{var}\, g$ (see text). Insets show device micrographs.

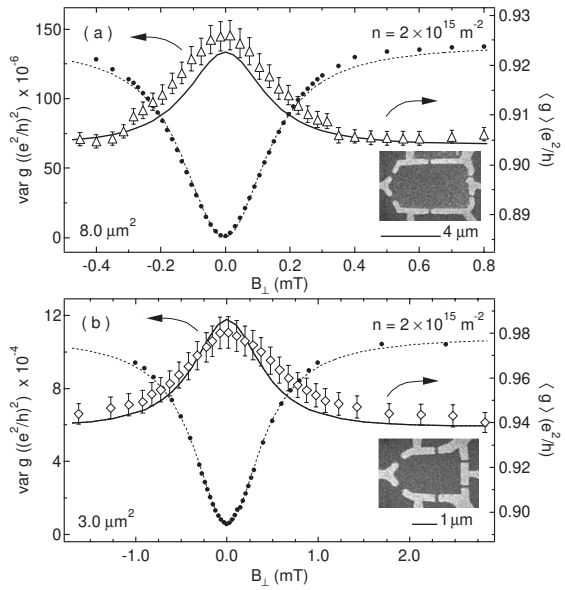

FIG. 2: Conductance average $\langle g(B_\perp)\rangle$ (solid dots) and variance $\mathrm{var}\, g(B_\perp)$ (open triangles and diamonds) as a function of perpendicular field $B_\perp$ with $B_k = 0$, for (a) large and (b) small dot, both fabricated on low density material. Both devices display weak localization in $\langle g(B_\perp)\rangle$. Fits to RMT is shown as dashed and solid curves, as described in the caption of Fig. 1. Insets show device micrographs; geometry of large device is identical to large dot in high density material.

Figs. 1 and 2 insets). The lower density wafer showed weak localization at $B_k = 0$ [10], while the higher density material has sufficient SO coupling to exhibit antilocalization at B_k [4]. Further details of these wafers are given in [4, 10]. Measurements were made in a ^{3}He cryostat at 0.3 K using current bias of 1 nA at 338 Hz. In order to apply tesla-scale B_k while maintaining sub-gauss control of $B_\perp$, we mount the sample with the 2DEG aligned to the axis of the primary solenoid (accurate to $\quad 1$) and use an independent split-coil magnet attached to the cryostat to provide $B_\perp$ [3]. The Hall voltage measured in a co-mounted Hall bar sample as well as the symmetry of transport through the dot itself (visible for $B_k < 2$T) was used to locate $B_\perp = 0$ as it changed with B_k.

Statistics of conductance fluctuations were gathered using two shape-distorting gates [18] while the point contacts were actively held at one fully transmitting mode each. At each value of $B_\perp$ and B_k, mean and variance were estimated based on $\quad 400$ ($\quad 200$) statistically independent samples for the low density (high density) dots. For $\mathrm{var}\, g(B_k; B_\perp \neq 0)$ data with TRS explicitly broken, $B_\perp$ was used to gather additional samples to reduced the statistical error.

Fitting the RMT results to $\langle g(B_\perp)\rangle$ yields values for the average SO length $_{so} = \sqrt{|_1\ _2|}$, where $_{1,2}$ are the SO lengths along the main crystal axes, as well as the phase coherence time $\ '$ and a geometrical parameter $_\perp$. The SO inhomogeneity $_{so} = \sqrt{|_1 / _2|}$ can be extracted from $\langle g(B_k)\rangle$ in the presence of antilocalization (AL), and is taken as $_{so} = 1.4\ (1.0)$ for the high (low) density devices [4]. An additional order-one geometrical parameter ^{0}, relevant for the strong SO regime and not readily extracted from transport measurements, is set to $^0 = 1$ for all devices. Further details of fits to the average conductance are given in Ref. [4]. We note that in absence of AL $_{so}$ can only be bounded from below. Values for $\ '$ are similar for all devices and consistent with previous measurements [19].

As seen in Figs. 1 and 2, all devices except the large high density dot show weak localization (WL), indicating these dots are in the regime $_{so}\quad L$, where SO effects are strongly suppressed by confinement. The observation of WL down to $\quad 40$ mK in previous measurements on identical devices [19] bounds the SO rate to $_{so} > 9$ m. We note that SO coupling of this order will noticeably re-

n	A	'	so	so	?	f_{var}		a	b
m ^{2}	m ^{2}	ns	m					ns ^{1}T ^{2}	ns ^{1}T ^{6}
2.0	3.0	0.18	8.5	1.0	0.15	1.0	2.8	0.5 0.1	0.028
2.0	8.0	0.21	8.5	1.0	0.25	0.6	3.0	0.37 0.07	0.028
5.8	1.2	0.10	3.2	1.4	0.33	1.9	1.0	6.6 1	0.14
5.8	8.0	0.39	4.4	1.4	0.23	0.7	0.45	1.4 0.4	0.14

TABLE I: Carrier density n, dot area $A = L^2$, coherence time $\ '$, spin-orbit parameters $_{so}$ and $_{so}$, RMT parameters $_\perp$, f_{var} and and FJ parameters a and b, see text.

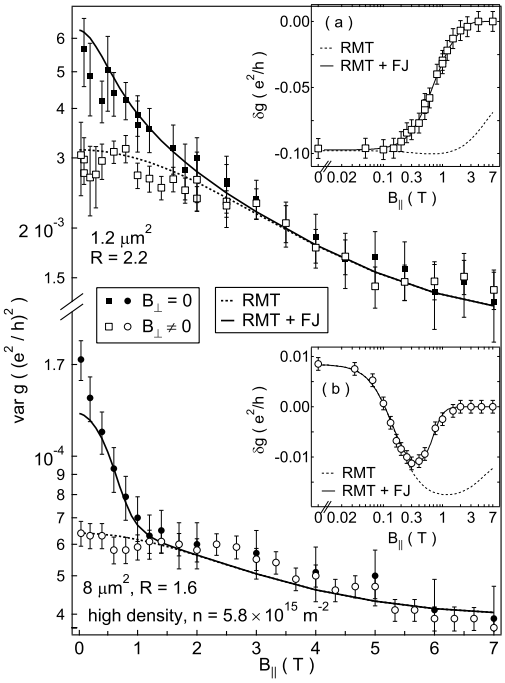

FIG. 3: Variance of conductance fluctuations, var g, in high density dots, as a function of in-plane field B_k with $B_? \neq 0$ sufficient to break TRS (open symbols) and $B_? = 0$ (solid symbols). The big dot shows less reduction in var g ($B_? \neq 0$) with B_k than the small dot, consistent with RMT, see text. Insets show quantum correction to average conductance, $g(B_k) = hg(B_? = 0; B_k)i \; hg(B_? \neq 0; B_k)i$. In both main figure and insets, dashed curves are fits to RMT, solid curves (labeled RMT+FJ) are fits to RMT including orbital coupling of B_k, see text.

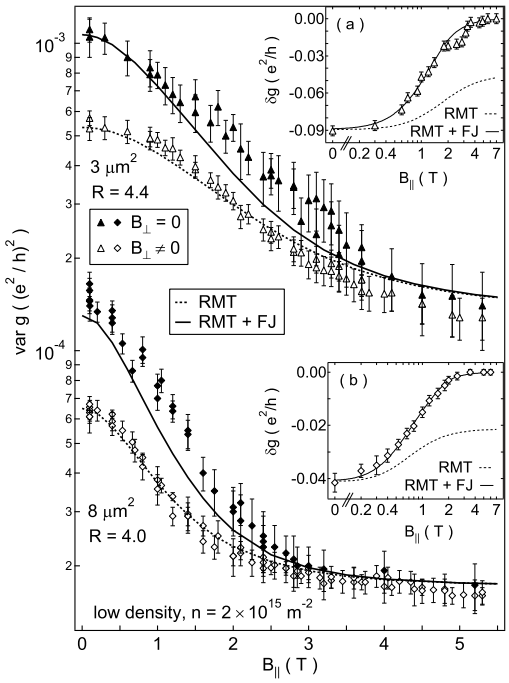

FIG. 4: As in Fig. 3, but for low density dots. In this case, the larger dot has a larger reduction factor in parallel field, consistent with RMT (curves). Orbital coupling of B_k breaks TRS, making var g independent of $B_?$ and quenching the quantum correction to average conductance, $g \; ! \; 0$, (insets) on the same (dot-size-dependent) scale of B_k

duce the low-temperature WL feature and therefore contribute to the saturation of WL observed in Ref. [19].

For both the high and low density material (respectively with AL and WL), var g at $B_k = 0$ is reduced upon application of a TRS-breaking perpendicular field, as seen in Figs. 1 and 2. This effect has been investigated previously for the weak SO (WL) case [18, 20], and has been observed but not analyzed for the strong SO (AL) case [4]. The solid theory curves in Figs. 1, 2 include thermal smearing and decoherence effects and use parameters obtained from fits of RMT to $hg(B_?)i$, plus one additional parameter, f_{var}, (Table 1) to normalize the var g ($B_? \neq 0$) the RMT value. This factor compensates the assumption of multimode leads, $N \quad 1$, in the RMT [1], whereas the experiment has $N = 2$. RMT for var g in the case $N = 2$ case has been given, but does not include SO or Zeeman terms [21].

We next investigate the effect of an in-plane magnetic field on var g, focusing first on the case where TRS is broken by a small perpendicular field, $B_? \neq 0$. As seen in Figs. 3 and 4, var g ($B_? \neq 0; B_k$) decreases with increasing B_k, and saturates at large B_k, giving reduction factors $R = \text{var}g(B_? \neq 0; B_k = 0)/\text{var}g(B_? \neq 0; B_k \quad 0)$ between $R \quad 1.6$ for the large high-density dots (which show AL at $B_k = 0$) and $R \quad 4$ for large low-density dots (which show WL at $B_k = 0$). This range of values for R can be readily interpreted within RMT: For the large high density dots (relatively strong SO coupling, not suppressed by confinement), Kramers degeneracy is broken whenever TRS is broken, and there is weak spin mixing (= 2; s = 1; 1 < < 2) at $B_k = 0$. The effect of B_k is to fully mix the Kramers pair (= 2; s = 1; = 1), thus the reduction $1 \quad R \quad 2$. On the other hand, dots showing WL at $B_k = 0$ retain spin degeneracy (= 2; s = 2; = 2) at $B_k = 0$, which is then lifted by Zeeman coupling (= 2; s = 1; = 2) and at larger B_k mixed (= 2; s = 1; = 1) due to SO coupling revived by B_k, giving $R \quad 4$.

Spin mixing induced by B_k, marking the = 1 to 2 crossover, occurs when a field-dependent energy scale $_?^Z$ exceeds the level broadening $\sim = h(\,_{esc}^{1} + \,_{,}^{1})^{1}$ ($\,_{esc}^{1} = N \;/h$ is the escape rate from the dot). This new energy scale depends on both Zeeman and SO coupling, $_?^Z = \,^2\,_Z^2/(2E_T)(A/\,_{so}^2)$ [1], where $_Z = g\,_B B$ is the Zeeman splitting, E_T is the Thouless energy (for ballistic dots $E_T \quad h v_F/\sqrt{A}$, where v_F is the Fermi velocity), and is a parameter of order one that depends on dot geometry as well as the direction of B_k [1, 2]. Note that $_?^Z/\sim \; / \,_Z^2 A^{5/2}$ (when $_{esc} \quad ,$) so that the = 1 to 2 crossover field will depend on dot size. For the smallest dot, the crossover is inaccessible, and = 1 for all measured fields and $R \quad 2$ due to breaking of Kramers degeneracy only

($s = 2$ to 1). In the low density dots, the $= 1$ to 2 crossover is accessible, occurring around B_k 1(3) T for the larger (smaller) dot. The large high density dot has $1 < < 2$ already at $B_k = 0$ due to SO coupling, and the crossover to $= 2$ occurs around B_k 3 T. Because of the undetermined coefficient , the SO length $_{so}$ cannot be independently extracted from $\mathrm{var}\,g(B_k)$. Taking as a single fit parameter, the dashed curves in Figs. 3 and 4 give the RMT results, which are in good agreement with experiment for all devices.

Finally, we investigate orbital effects of B_k on var g, measured when TRS is not explicitly broken by a perpendicular field ($B_\perp = 0$). Figures 3 and 4 show that as B_k is increased, $\mathrm{var}\,g(B_\perp = 0; B_k)$ decreases sharply, approaching $\mathrm{var}\,g(B_\perp \neq 0; B_k)$. At large B_k, var g becomes independent of $B_\perp$ whereas RMT gives $\mathrm{var}\,g_{RMT}(B_\perp = 0)/\mathrm{var}\,g_{RMT}(B_\perp \neq 0) = 2$ for all B_k. On a similar scale of B_k, WL corrections $g(B_k) = \langle g(B_\perp = 0; B_k)\rangle \langle g(B_\perp \neq 0; B_k)\rangle$ are also vanishing in all devices whereas RMT predicts a finite g. As discussed previously [3, 4, 10], these effects result from the breaking of TRS by B_k [8, 9].

Following Ref. [8] (FJ), we account for the suppression of $g(B_k)$ and $\mathrm{var}\,g(B_k)$ by introducing a field-dependent factor $f_{FJ}(B_k) = (1 + {}^{1}_{Bk}/{}^{1}_{esc})^{1}$, where ${}^{1}_{Bk}$ $aB_k^2 + bB_k^6$. The B_k^2 term reflects interface roughness and dopant inhomogeneities; the B_k^6 term is due to the asymmetry of the well. The RMT results are then modified as $g(B_k) = g_{RMT}(B_k) f_{FJ}(B_k)$ and $\mathrm{var}\,g(B_\perp = 0; B_k) = \mathrm{var}\,g_{RMT}(B_\perp \neq 0; B_k)(1 + f_{FJ}(B_k))$ to account for flux effects of the parallel field [22]. The coefficient a is obtained from a fit to the experimental $g(B_k)$ while b is estimated from device simulations [22] (Table I). The resulting theory curves for both $g(B_k)$ (solid curves, insets Figs. 3 and 4) and $\mathrm{var}\,g(B_\perp = 0; B_k)$ (solid curves, main panels) are in good agreement with experiment. We emphasize that the theoretical variance curves $\mathrm{var}\,g(B_\perp = 0; B_k)$ are not fit. Estimates of a; b based on correlation functions of parallel-field conductance fluctuations [10] are consistent with the values obtained here based on $g(B_k)$.

In summary, mesoscopic conductance fluctuations in open quantum dots in presence of SO coupling and in-plane fields can be understood in terms of fundamental symmetries in the system, including novel partially broken spin rotation symmetries as well as time reversal symmetry, which can be broken by both perpendicular and in-plane fields.

We thank I. Aleiner, B. Altshuler, P. Brouwer, J. Cremers, V. Fal'ko, J. Folk, B. Halperin, T. Jungwirth and Y. Lyanda-Geller. This work was supported in part by DARPA-QuIST, DARPA-SpinS, ARO-MURI and NSF-NSEC. We also acknowledge support from ND-SEG (J.B.M.) and the Harvard Society of Fellows (D.G.-G). Work at UCSB was supported by QUEST, an NSF Science and Technology Center.

[1] I. L. Aleiner et al., Phys. Rev. Lett. 87, 256801 (2001); J. N. H. J. Cremers et al., Phys. Rev. B 68, 125329 (2003).
[2] B. I. Halperin et al., Phys. Rev. Lett. 86, 2106 (2001).
[3] J. A. Folk et al., Phys. Rev. Lett. 86, 2102 (2001).
[4] D. M. Zumbuhl et al., Phys. Rev. Lett. 89, 276803 (2002).
[5] A. V. Khaetskii et al., Phys. Rev. B 61, 12639 (2000); Y. V. Nazarov, Phys. Rev. B 64, 2001 (2001).
[6] T. Fujisawa et al., Nature 419, 278 (2002); J. M. Elzerman et al., Nature 430, 431 (2004); V. Golovach et al., Phys. Rev. Lett. 93, 16601 (2004).
[7] P. W. Brouwer, et al., Phys. Rev. B 65, R81302 (2002).
[8] V. I. Fal'ko et al., Phys. Rev. B 65, 81306 (2002).
[9] J. S. Meyer, et al. Phys. Rev. Lett. 89, 206601 (2002).
[10] D. M. Zumbuhl et al., Phys. Rev. B 69, 121305R (2004).
[11] A. G. Mal'shukov et al., Phys. Rev. B 56, 6436 (1997); G. M. Minkov et al., Phys. Rev. B 70, 155323 (2004).
[12] F. E. Meijer et al., Phys. Rev. B 70, 201307R (2004); F. E. Meijer et al., cond-mat/0412731 (2004).
[13] Y. Meir et al., Phys. Rev. Lett. 63, 798 (1989).
[14] Y. B. Lyanda-Geller et al., Phys. Rev. Lett. 72, 1894 (1994).
[15] B. L. Al'tshuler, JETP Lett. 41, 648 (1985); B. L. Al'tshuler et al., Sov. Phys. JETP 64, 127 (1986); S. Feng, Phys. Rev. B 39, 8722 (1989); A. D. Stone, Phys. Rev. B 39, 10736 (1989); C. W. J. Beenakker, Rev. Mod. Phys. 69, 731 (1997).
[16] N. O. Birge et al., Phys. Rev. Lett. 62, 195 (1989); P. Debray et al., Phys. Rev. Lett. 63, 2264 (1989); O. Millo et al., Phys. Rev. Lett. 65, 1494 (1990); Y. K. Fukai et al., Solid State Comm. 94, 757 (1995); J. S. Moon et al., Phys. Rev. B 56, 15124 (1997).
[17] B. Hackens et al., Physica E 12, 833 (2002). C. Gustin et al., Physica E 17, 154 (2003a).
[18] I. H. Chan et al., Phys. Rev. Lett. 74, 3876 (1995).
[19] A. G. Huibers et al., Phys. Rev. Lett. 81, 200 (1998); 83, 5090 (1999).
[20] A. G. Huibers et al., Phys. Rev. Lett. 81, 1917 (1998).
[21] E. R. P. Alves et al., Phys. Rev. Lett. 88, 256805 (2002).
[22] V. Fal'ko and T. Jungwirth, (private communication).